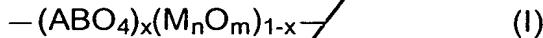


*Cond  
B2*  
oxide layer. Gusev *et al.* propose that it is possible to deposit aluminum oxide on hydrogen-terminated silicon without forming an interfacial layer using NRP, medium energy ion scattering (MEIS), and high-resolution transmission electron microscopy (TEM).--

**In the Claims:**

Please replace Claim 1 with the following amended claim:

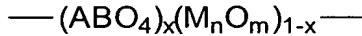
1. (Amended) A non-crystalline oxide represented by the formula (I):



wherein:  
A is an element selected from Group IIIA of the periodic table;  
B is an element selected from Group VB of the periodic table;  
O is oxygen;  
M is an element selected from either Group IIIB or Group IVB of the periodic table; and  
n ranges from about 0.5 to about 2.5, m ranges from about 1.5 to about 3.5, and  
 $0 < x < 1$ .

Please replace Claim 4 with the following amended claim:

4. (Amended) A method of forming a non-crystalline oxide represented by the formula (I):



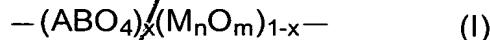
wherein A is an element selected from Group IIIA of the periodic table, B is an element selected from Group VB of the periodic table, O is oxygen, M is an element selected from either Group IIIB or Group IVB of the periodic table, n ranges from about 0.5 to about 2.5, m ranges from about 1.5 to about 3.5, and  $0 < x < 1$ , said method comprising:

delivering a gaseous source comprising element A, a gaseous source comprising element B, a gaseous source comprising element M, and a gaseous source comprising oxygen on a substrate such that the gaseous source comprising element A, the gaseous source comprising

*Cond B4*  
element B, the gaseous source comprising element M, and the gaseous source comprising oxygen react to form the non-crystalline oxide.

*B5*  
Please replace Claim 11 with the following amended claim:

11. (Amended) A field effect transistor comprising:  
an integrated circuit substrate having a first surface;  
source and drain regions in said substrate at said first surface in a  
spaced apart relationship; and  
a gate insulating layer on said substrate at said first surface between said spaced apart  
source and drain regions, said gate insulating layer comprising a non-crystalline oxide  
represented by the formula (I):



wherein:

A is an element selected from Group IIIA of the periodic table;  
B is an element selected from Group VB of the periodic table;  
O is oxygen;  
M is an element selected from either Group IIIB or Group IVB of the periodic table;  
n ranges from about 0.5 to about 2.5;  
m ranges from about 1.5 to about 3.5; and  
 $0 < x < 1.$

*B6*  
*MB D3*  
Please replace Claim 24 with the following amended claim:

24. (Amended) A non-crystalline oxide represented by the formula (II):



wherein:

Al is aluminum;